

## DIE SPECIFICATION

### 60V 300mA MONOLITHIC DIODE ARRAY

#### FEATURES:

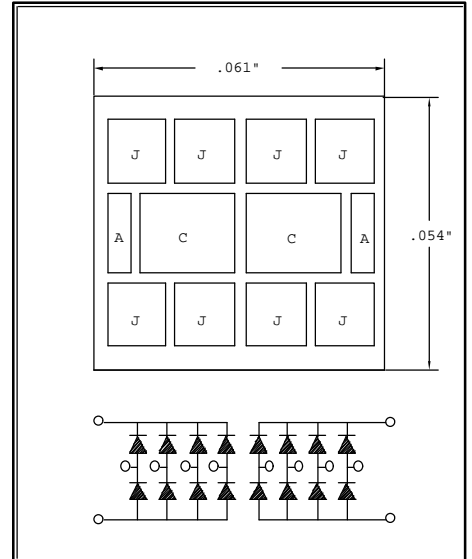
- TWO EIGHT DIODE CORE DRIVER
- $t_{rr} < 20 \text{ ns}$
- RUGGED AIR-ISOLATED CONSTRUCTION
- LOW REVERSE LEAKAGE CURRENT

#### Absolute Maximum Ratings:

Symbol	Parameter	Limit	Unit
VBR(R)	*1 *2 Reverse Breakdown Voltage	60	Vdc
IO	*1 Continuous Forward Current	300	mAdc
IFSM	*1 Peak Surge Current ( $t_p = 1/120 \text{ s}$ )	500	mAdc
Top	Operating Junction Temperature Range	-65 to +150	°C
Tstg	Storage Temperature Range	-65 to +200	°C

NOTE 1: Each Diode

NOTE 2: Pulsed: PW = 100ms max.; duty cycle  $\leq 20\%$



#### Electrical Characteristics (Per Diode) @ 25°C unless otherwise specified

Symbol	Parameter	Conditions	Min	Max	Unit
BV1	Breakdown Voltage	IR = 10uAdc	60		
Vf1	Forward Voltage	IF = 100mAdc *1		1	Vdc
Vf2	Forward Voltage	IF = 500mAdc *1		1.5	Vdc
IR1	Reverse Current	VR = 40 Vdc		0.1	uAdc
Ct	Capacitance (pin to pin)	VR = 0 Vdc ; f = 1 MHz		8.0	pF
tfr	Forward Recovery Time	IF = 500mAdc		40	ns
trr	Reverse Recovery Time	IF = IR = 200mAdc, irr = 20 mAdc, RL = 100 ohms		20	ns

NOTE 1: Pulsed: PW = 300us +/- 50us, duty cycle  $\leq 2\%$ , 90us after leading edge

#### Packaging Options:

W: Wafer (100% probed) U: Wafer (sample probed)  
D: Chip (Waffle Pack) B: Chip (Vial)  
V: Chip (Waffle Pack, 100% visually inspected) X: Other

#### Processing Options:

Standard: Capable of JANTXV application (No Suffix)  
Suffix C: Commercial  
Suffix S: Capable of S-Level equivalent applications

#### Metallization Options:

Standard: Al Top / Au Backside (No Dash #)

#### ORDERING INFORMATION

PART #: 28M0\_\_-\_\_  
First Suffix Letter: Packaging Option  
Second Suffix Letter: Processing Option  
Dash #: Metallization Option

Sertech reserves the right to make changes to any product design, specification or other information at any time without prior notice.